

NTD110N02R, STD110N02R

Power MOSFET

24 V, 110 A, N-Channel DPAK

Features

- Planar HD3e Process for Fast Switching Performance
- Low $R_{DS(on)}$ to Minimize Conduction Loss
- Low C_{iss} to Minimize Driver Loss
- Low Gate Charge
- Optimized for High Side Switching Requirements in High-Efficiency DC-DC Converters
- AEC Q101 Qualified – STD110N02R
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	24	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	V
Thermal Resistance – Junction-to-Case	$R_{\theta JC}$	1.35	$^\circ\text{C/W}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_D	110	W
Drain Current	I_D	110	A
– Continuous @ $T_C = 25^\circ\text{C}$, Chip	I_D	110	A
– Continuous @ $T_C = 25^\circ\text{C}$	I_D	110	A
Limited by Package	I_D	32	A
– Continuous @ $T_A = 25^\circ\text{C}$	I_D	32	A
Limited by Wires	I_D	110	A
– Single Pulse ($t_p = 10 \mu\text{s}$)	I_D	110	A
Thermal Resistance	$R_{\theta JA}$	52	$^\circ\text{C/W}$
– Junction-to-Ambient (Note 1)	P_D	2.88	W
– Total Power Dissipation @ $T_A = 25^\circ\text{C}$	I_D	17.5	A
– Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	17.5	A
Thermal Resistance	$R_{\theta JA}$	100	$^\circ\text{C/W}$
– Junction-to-Ambient (Note 2)	P_D	1.5	W
– Total Power Dissipation @ $T_A = 25^\circ\text{C}$	I_D	12.5	A
– Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	12.5	A
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 50 \text{ Vdc}$, $V_{GS} = 10 \text{ Vdc}$, $I_L = 15.5 \text{ Apk}$, $L = 1.0 \text{ mH}$, $R_G = 25 \Omega$)	E_{AS}	120	mJ
Maximum Lead Temperature for Soldering Purposes, (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. When surface mounted to an FR4 board using 0.5 sq in drain pad size.
2. When surface mounted to an FR4 board using the minimum recommended pad size.

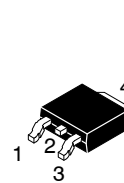
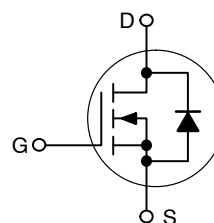


ON Semiconductor®

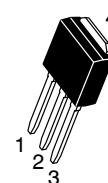
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
24 V	4.1 m Ω @ 10 V	110 A

N-Channel

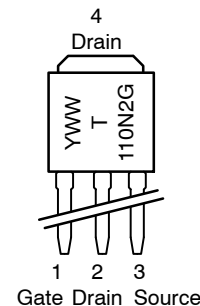
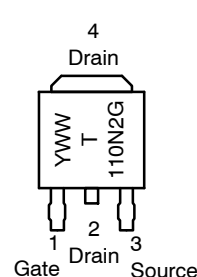


CASE 369AA
DPAK
(Surface Mount)
STYLE 2



CASE 369D
DPAK
(Straight Lead)
STYLE 2

MARKING DIAGRAM & PIN ASSIGNMENTS



Y = Year
WW = Work Week
T110N2 = Device Code
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTD110N02R, STD110N02R

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (Note 3) (V _{GS} = 0 V, I _D = 250 μA)	V _{(BR)DSS}	24	28		V
Positive Temperature Coefficient			15		mV/°C
Zero Gate Voltage Drain Current (V _{DS} = 20 V, V _{GS} = 0 V) (V _{DS} = 20 V, V _{GS} = 0 V, T _J = 125°C)	I _{DSS}			1.5 10	μA
Gate-Body Leakage Current (V _{GS} = ±20 V, V _{DS} = 0 V)	I _{GSS}			±100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage (Note 3) (V _{DS} = V _{GS} , I _D = 250 μA)	V _{GS(th)}	1.0	1.5 5.0	2.0	V mV/°C
Negative Threshold Temperature Coefficient					
Static Drain-to-Source On-Resistance (Note 3) (V _{GS} = 10 V, I _D = 110 A) (V _{GS} = 4.5 V, I _D = 55 A) (V _{GS} = 10 V, I _D = 20 A) (V _{GS} = 4.5 V, I _D = 20 A)	R _{DS(on)}		4.1 5.5 3.9 5.5	4.6 6.2	mΩ
Forward Transconductance (V _{DS} = 10 V, I _D = 15 A) (Note 3)	g _{FS}		44		Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = 20 V, V _{GS} = 0 V, f = 1.0 MHz)	C _{iss}		2710	3440	pF
Output Capacitance		C _{oss}		1105	1670	
Transfer Capacitance		C _{rss}		450	640	

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	(V _{GS} = 10 V, V _{DD} = 10 V, I _D = 40 A, R _G = 3.0 Ω)	t _{d(on)}		11	22	ns
Rise Time		t _r		39	80	
Turn-Off Delay Time		t _{d(off)}		27	40	
Fall Time		t _f		21	40	
Gate Charge	(V _{GS} = 4.5 V, I _D = 40 A, V _{DS} = 10 V) (Note 3)	Q _T		23.6	28	nC
		Q _{GS}		5.1		
		Q _{GD}		11		

SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage	(I _S = 20 A, V _{GS} = 0 V) (Note 3) (I _S = 55 A, V _{GS} = 0 V) (I _S = 20 A, V _{GS} = 0 V, T _J = 125°C)	V _{SD}		0.82 0.99 0.65	1.2	V
Reverse Recovery Time	(I _S = 30 A, V _{GS} = 0 V, di _S /dt = 100 A/μs) (Note 3)	t _{rr}		36.5		ns
		t _a		30		
		t _b		25		
Reverse Recovery Stored Charge		Q _{rr}		0.048		μC

- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

NTD110N02R, STD110N02R

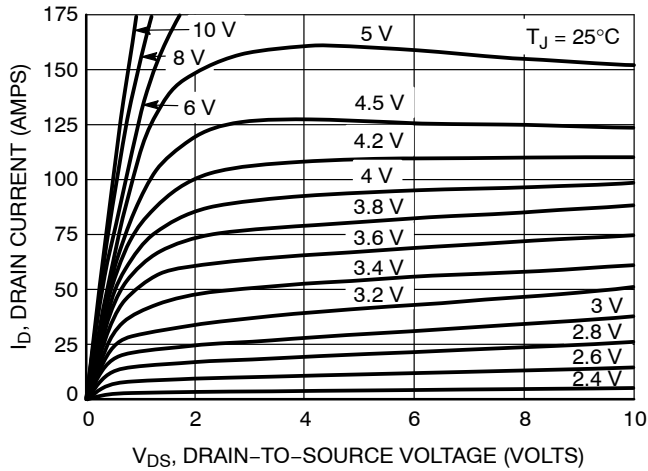


Figure 1. On-Region Characteristics

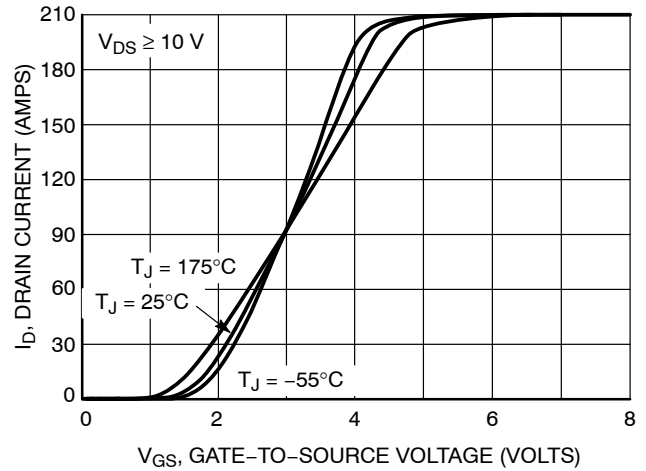


Figure 2. Transfer Characteristics

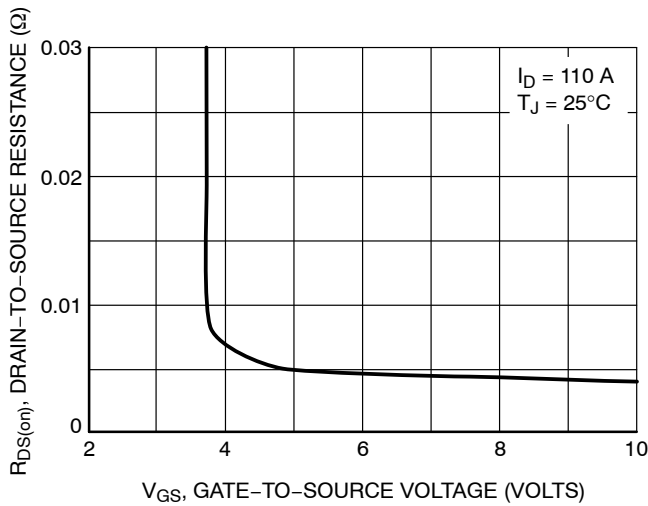


Figure 3. On-Resistance versus Gate-to-Source Voltage

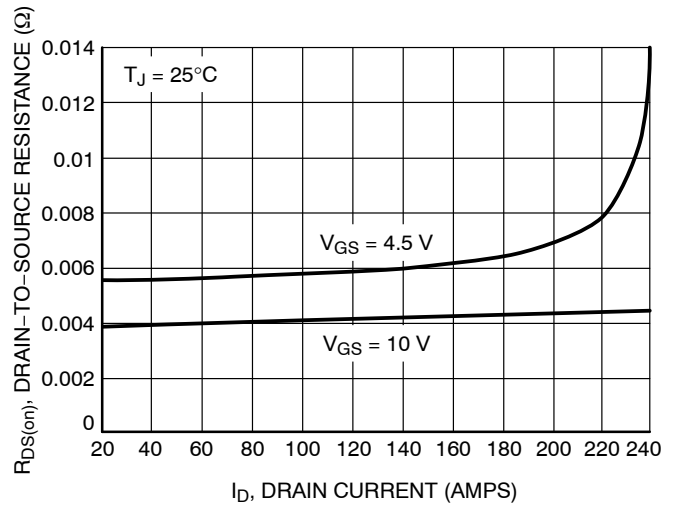


Figure 4. On-Resistance versus Drain Current and Gate Voltage

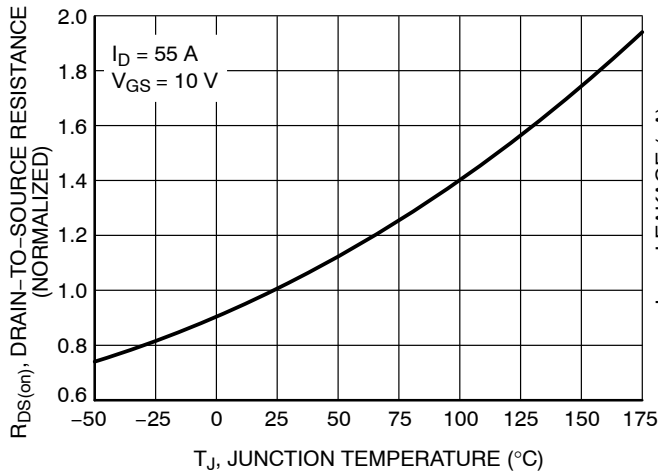


Figure 5. On-Resistance Variation with Temperature

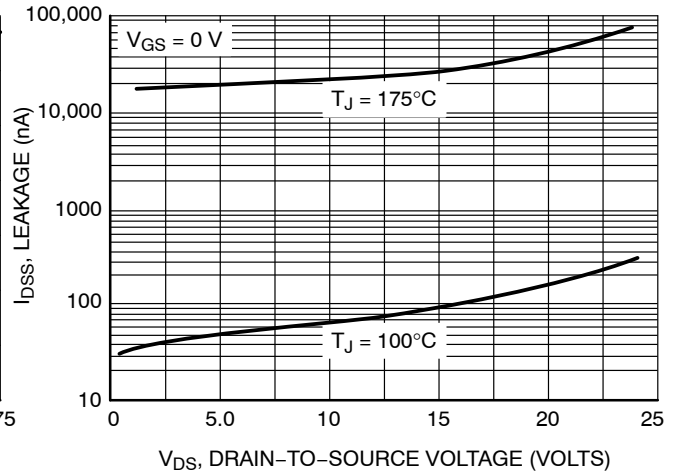
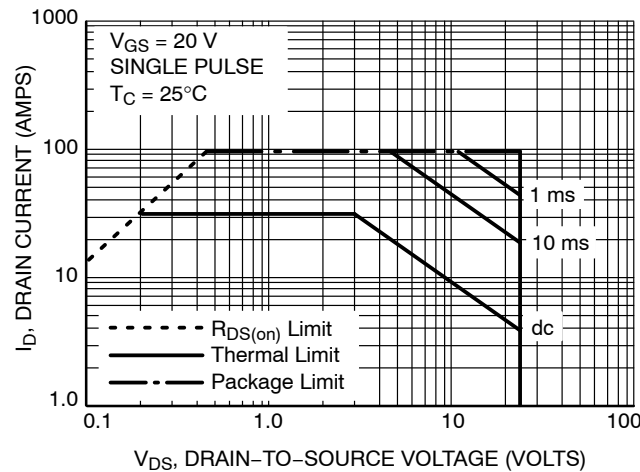
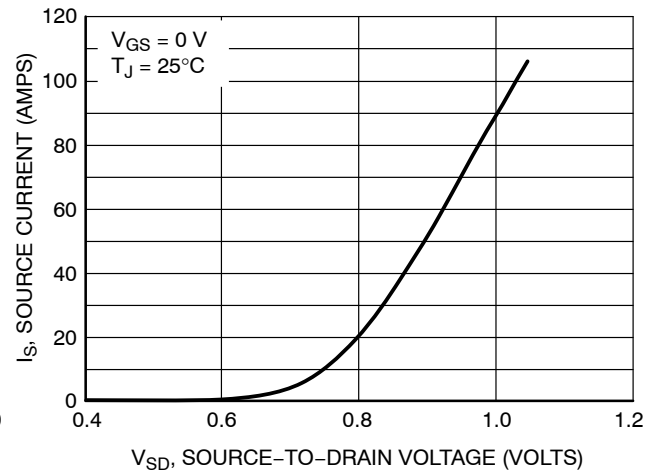
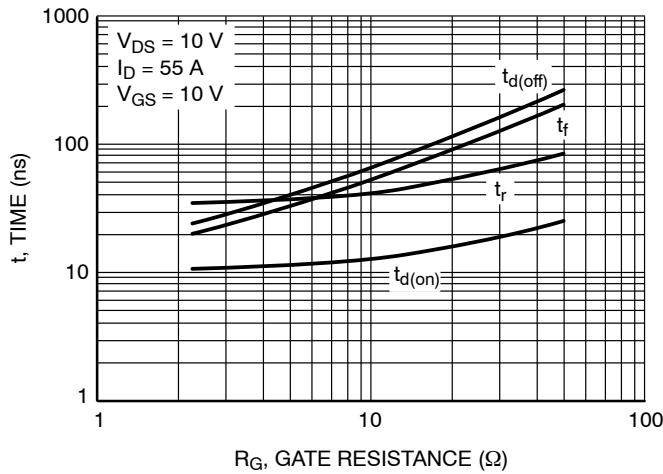
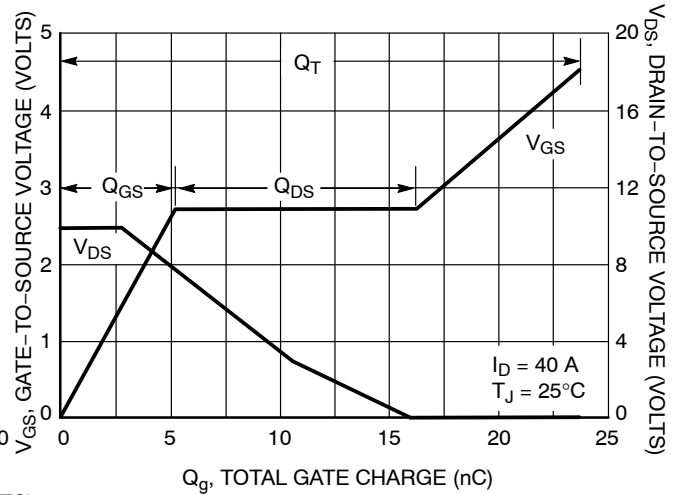
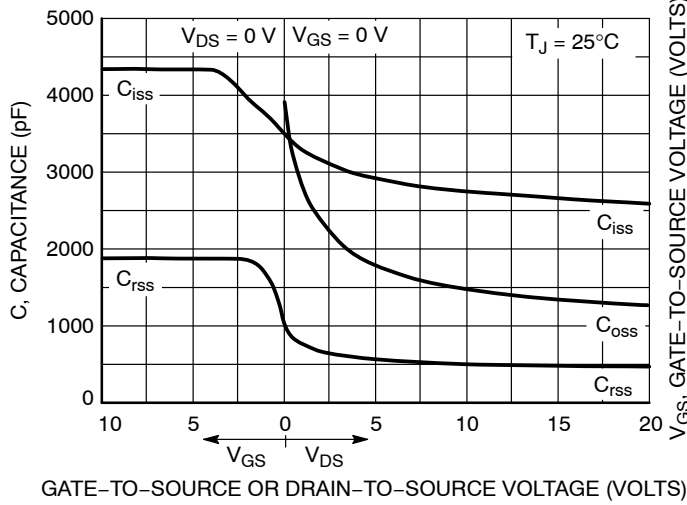


Figure 6. Drain-to-Source Leakage Current versus Voltage

NTD110N02R, STD110N02R



NTD110N02R, STD110N02R

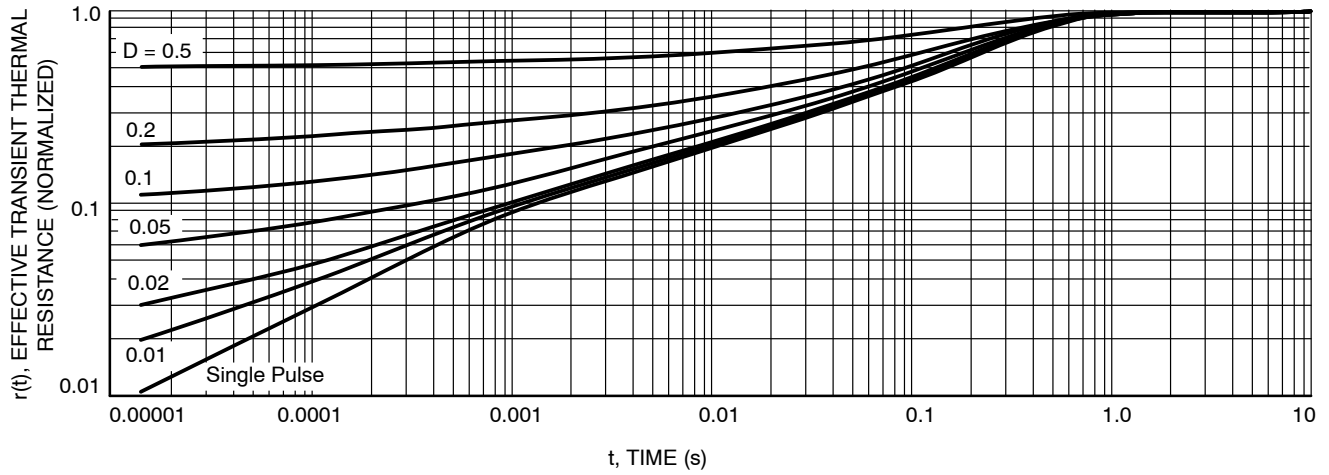


Figure 12. Thermal Response

ORDERING INFORMATION

Device	Package	Shipping [†]
NTD110N02RT4G	DPAK (Pb-Free)	2500 / Tape & Reel
STD110N02RT4G	DPAK (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

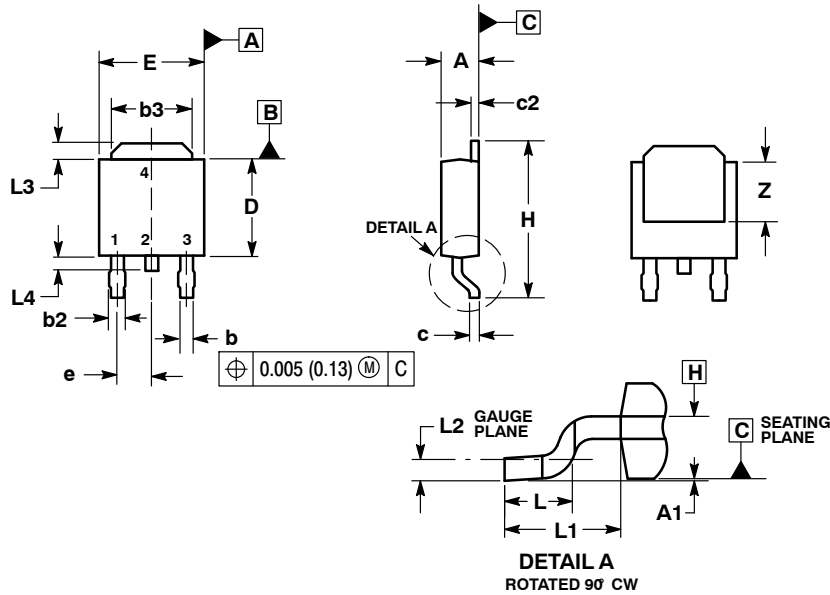
NTD110N02R, STD110N02R

PACKAGE DIMENSIONS

DPAK (SINGLE GUAGE)

CASE 369AA-01

ISSUE B

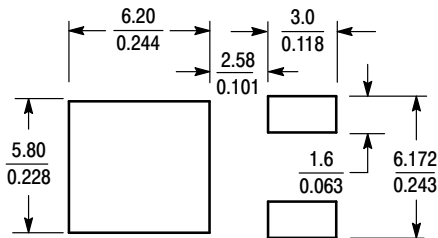


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}} \right)$

STYLE 2:

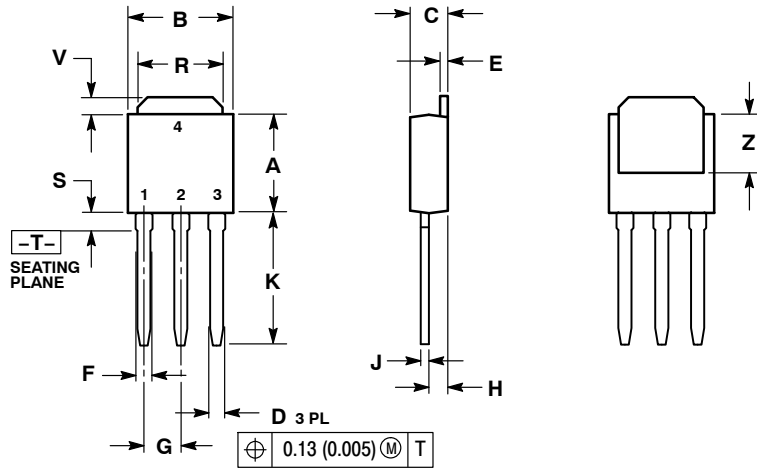
1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NTD110N02R, STD110N02R

PACKAGE DIMENSIONS

IPAK CASE 369D-01 ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative

NTD110N02R/D

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9